



## N-CHANNEL MOSFET

**Qualified per MIL-PRF-19500/543**

Qualified Levels:  
JAN, JANTX, and  
JANTXV

### DESCRIPTION

This family of 2N6764, 2N6766, 2N6768 and 2N6770 switching transistors are military qualified up to the JANTXV level for high-reliability applications. These devices are also available in a thru hole TO-254AA leaded package. Microsemi also offers numerous other transistor products to meet higher and lower power ratings with various switching speed requirements in both through-hole and surface-mount packages.

**Important:** For the latest information, visit our website <http://www.microsemi.com>.

### FEATURES

- JEDEC registered 2N6764, 2N6766, 2N6768 and 2N6770 number series.
- JAN, JANTX, and JANTXV qualifications are available per MIL-PRF-19500/543. (See [part nomenclature](#) for all available options.)
- RoHS compliant versions available (commercial grade only).

### APPLICATIONS / BENEFITS

- Low-profile metal can design.
- Military and other high-reliability applications.

### MAXIMUM RATINGS @ T<sub>A</sub> = +25 °C unless otherwise stated

Parameters / Test Conditions	Symbol	Value	Unit
Junction & Storage Temperature Range	T <sub>J</sub> & T <sub>stg</sub>	-55 to +150	°C
Thermal Resistance Junction-to-Case	R <sub>θJC</sub>	0.83	°C/W
Total Power Dissipation	P <sub>T</sub>	4 150	W
		@ T <sub>A</sub> = +25 °C @ T <sub>C</sub> = +25 °C <sup>(1)</sup>	
Drain-Source Voltage, dc	V <sub>DS</sub>	100 200 400 500	V
		2N6764 2N6766 2N6768 2N6770	
Gate-Source Voltage, dc	V <sub>GS</sub>	± 20	V
Drain Current, dc @ T <sub>C</sub> = +25 °C <sup>(2)</sup>	I <sub>D1</sub>	38.0 30.0 14.0 12.0	A
		2N6764 2N6766 2N6768 2N6770	
Drain Current, dc @ T <sub>C</sub> = +100 °C <sup>(2)</sup>	I <sub>D2</sub>	24.0 19.0 9.0 7.75	A
		2N6764 2N6766 2N6768 2N6770	
Off-State Current (Peak Total Value) <sup>(3)</sup>	I <sub>DM</sub>	152 120 56 48	A (pk)
		2N6764 2N6766 2N6768 2N6770	
Source Current	I <sub>S</sub>	38.0 30.0 14.0 12.0	A
		2N6764 2N6766 2N6768 2N6770	

Notes featured on next page.



**TO-204AE (TO-3)  
Package**

Also available in:

**TO-254AA package**  
(leaded)



[2N6764T1 & 2N6770T1](#)

**MSC – Lawrence**

6 Lake Street,  
Lawrence, MA 01841  
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[www.microsemi.com](http://www.microsemi.com)

- NOTES:**
- Derate linearly by 1.2 W/°C for  $T_c > +25$  °C.
  - The following formula derives the maximum theoretical  $I_D$  limit.  $I_D$  is limited by package and internal wires and may also be limited by pin diameter:

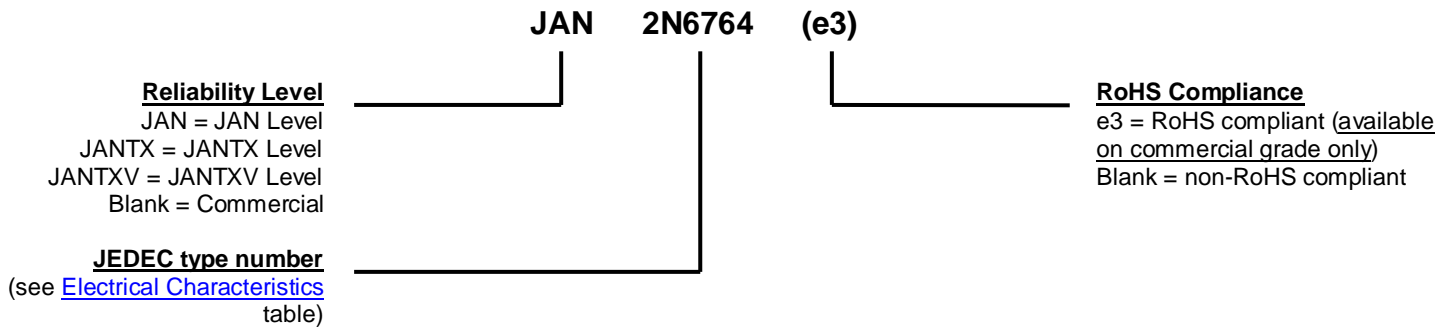
$$I_D = \sqrt{\frac{T_J(\max) - T_c}{R_{\theta JC} \times R_{DS(on)} @ T_J(\max)}}$$

- $I_{DM} = 4 \times I_{D1}$  as calculated in note 2.

### MECHANICAL and PACKAGING

- CASE: TO-3 metal can.
- TERMINALS: Solder dipped (Sn63/Pb37) over nickel plated alloy 52. RoHS compliant matte-tin plating is also available on commercial grade only.
- MARKING: Manufacturer's ID, part number, date code.
- WEIGHT: Approximately 12.7 grams.
- See [Package Dimensions](#) on last page.

### PART NOMENCLATURE



### SYMBOLS & DEFINITIONS

Symbol	Definition
$di/dt$	Rate of change of diode current while in reverse-recovery mode, recorded as maximum value.
$I_F$	Forward current
$R_G$	Gate drive impedance
$V_{DD}$	Drain supply voltage
$V_{DS}$	Drain source voltage, dc
$V_{GS}$	Gate source voltage, dc

**ELECTRICAL CHARACTERISTICS @  $T_A = +25\text{ }^\circ\text{C}$ , unless otherwise noted**

Parameters / Test Conditions	Symbol	Min.	Max.	Unit
<b>OFF CHARACTERISTICS</b>				
Drain-Source Breakdown Voltage $V_{GS} = 0\text{ V}, I_D = 1.0\text{ mA}$	2N6764 2N6766 2N6768 2N6770 $V_{(BR)DSS}$	100 200 400 500		V
Gate-Source Voltage (Threshold) $V_{DS} \geq V_{GS}, I_D = 0.25\text{ mA}$ $V_{DS} \geq V_{GS}, I_D = 0.25\text{ mA}, T_J = +125\text{ }^\circ\text{C}$ $V_{DS} \geq V_{GS}, I_D = 0.25\text{ mA}, T_J = -55\text{ }^\circ\text{C}$	$V_{GS(th)1}$ $V_{GS(th)2}$ $V_{GS(th)3}$	2.0 1.0	4.0 5.0	V
Gate Current $V_{GS} = \pm 20\text{ V}, V_{DS} = 0\text{ V}$ $V_{GS} = \pm 20\text{ V}, V_{DS} = 0\text{ V}, T_J = +125\text{ }^\circ\text{C}$	$I_{GSS1}$ $I_{GSS2}$		$\pm 100$ $\pm 200$	nA
Drain Current $V_{GS} = 0\text{ V}, V_{DS} = 80\text{ V}$ $V_{GS} = 0\text{ V}, V_{DS} = 160\text{ V}$ $V_{GS} = 0\text{ V}, V_{DS} = 320\text{ V}$ $V_{GS} = 0\text{ V}, V_{DS} = 400\text{ V}$	2N6764 2N6766 2N6768 2N6770 $I_{DSS1}$		25	$\mu\text{A}$
Drain Current $V_{GS} = 0\text{ V}, V_{DS} = 100\text{ V}, T_J = +125\text{ }^\circ\text{C}$ $V_{GS} = 0\text{ V}, V_{DS} = 200\text{ V}, T_J = +125\text{ }^\circ\text{C}$ $V_{GS} = 0\text{ V}, V_{DS} = 400\text{ V}, T_J = +125\text{ }^\circ\text{C}$ $V_{GS} = 0\text{ V}, V_{DS} = 500\text{ V}, T_J = +125\text{ }^\circ\text{C}$	2N6764 2N6766 2N6768 2N6770 $I_{DSS2}$		1.0	mA
Drain Current $V_{GS} = 0\text{ V}, V_{DS} = 80\text{ V}, T_J = +125\text{ }^\circ\text{C}$ $V_{GS} = 0\text{ V}, V_{DS} = 160\text{ V}, T_J = +125\text{ }^\circ\text{C}$ $V_{GS} = 0\text{ V}, V_{DS} = 320\text{ V}, T_J = +125\text{ }^\circ\text{C}$ $V_{GS} = 0\text{ V}, V_{DS} = 400\text{ V}, T_J = +125\text{ }^\circ\text{C}$	2N6764 2N6766 2N6768 2N6770 $I_{DSS3}$		0.25	mA
Static Drain-Source On-State Resistance $V_{GS} = 10\text{ V}, I_D = 24.0\text{ A pulsed}$ $V_{GS} = 10\text{ V}, I_D = 19.0\text{ A pulsed}$ $V_{GS} = 10\text{ V}, I_D = 9.0\text{ A pulsed}$ $V_{GS} = 10\text{ V}, I_D = 7.75\text{ A pulsed}$	2N6764 2N6766 2N6768 2N6770 $r_{DS(on)1}$		0.055 0.085 0.3 0.4	$\Omega$
Static Drain-Source On-State Resistance $V_{GS} = 10\text{ V}, I_D = 38.0\text{ A pulsed}$ $V_{GS} = 10\text{ V}, I_D = 30.0\text{ A pulsed}$ $V_{GS} = 10\text{ V}, I_D = 14.0\text{ A pulsed}$ $V_{GS} = 10\text{ V}, I_D = 12.0\text{ A pulsed}$	2N6764 2N6766 2N6768 2N6770 $r_{DS(on)2}$		0.065 0.09 0.4 0.5	$\Omega$
Static Drain-Source On-State Resistance $T_J = +125\text{ }^\circ\text{C}$ $V_{GS} = 10\text{ V}, I_D = 24.0\text{ A pulsed}$ $V_{GS} = 10\text{ V}, I_D = 19.0\text{ A pulsed}$ $V_{GS} = 10\text{ V}, I_D = 9.0\text{ A pulsed}$ $V_{GS} = 10\text{ V}, I_D = 7.75\text{ A pulsed}$	2N6764 2N6766 2N6768 2N6770 $r_{DS(on)3}$		0.094 0.153 0.66 0.88	$\Omega$
Diode Forward Voltage $V_{GS} = 0\text{ V}, I_D = 38.0\text{ A pulsed}$ $V_{GS} = 0\text{ V}, I_D = 30.0\text{ A pulsed}$ $V_{GS} = 0\text{ V}, I_D = 14.0\text{ A pulsed}$ $V_{GS} = 0\text{ V}, I_D = 12.0\text{ A pulsed}$	2N6764 2N6766 2N6768 2N6770 $V_{SD}$		1.9 1.9 1.7 1.7	V

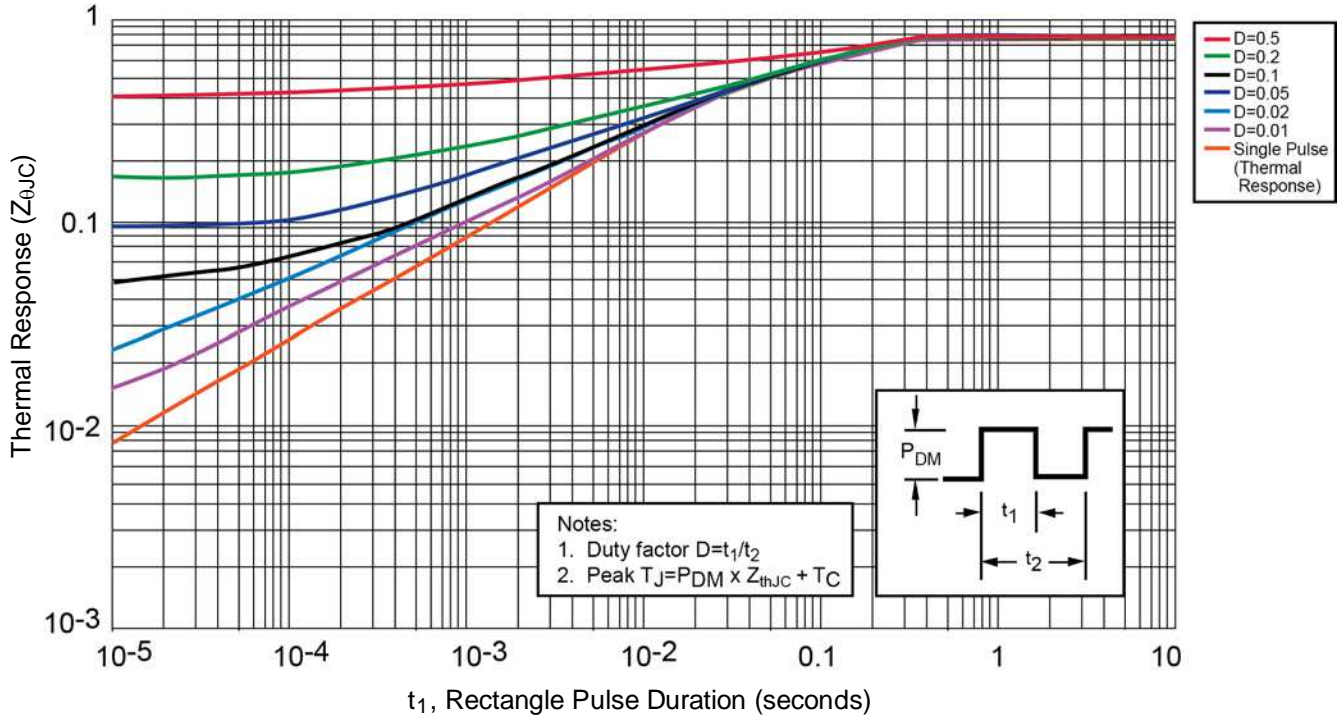
**ELECTRICAL CHARACTERISTICS @ T<sub>A</sub> = +25 °C, unless otherwise noted (continued)**
**DYNAMIC CHARACTERISTICS**

Parameters / Test Conditions	Symbol	Min.	Max.	Unit
<b>Gate Charge:</b>				
On-State Gate Charge	Q <sub>g(on)</sub>			nC
V <sub>GS</sub> = 10 V, I <sub>D</sub> = 38.0 A, V <sub>DS</sub> = 50 V 2N6764			125	
V <sub>GS</sub> = 10 V, I <sub>D</sub> = 30.0 A, V <sub>DS</sub> = 100 V 2N6766			115	
V <sub>GS</sub> = 10 V, I <sub>D</sub> = 14.0 A, V <sub>DS</sub> = 200 V 2N6768			110	
V <sub>GS</sub> = 10 V, I <sub>D</sub> = 12.0 A, V <sub>DS</sub> = 250 V 2N6770			120	
Gate to Source Charge	Q <sub>gs</sub>			nC
V <sub>GS</sub> = 10 V, I <sub>D</sub> = 38.0 A, V <sub>DS</sub> = 50 V 2N6764			22	
V <sub>GS</sub> = 10 V, I <sub>D</sub> = 30.0 A, V <sub>DS</sub> = 100 V 2N6766			22	
V <sub>GS</sub> = 10 V, I <sub>D</sub> = 14.0 A, V <sub>DS</sub> = 200 V 2N6768			18	
V <sub>GS</sub> = 10 V, I <sub>D</sub> = 12.0 A, V <sub>DS</sub> = 250 V 2N6770			19	
Gate to Drain Charge	Q <sub>gd</sub>			nC
V <sub>GS</sub> = 10 V, I <sub>D</sub> = 38.0 A, V <sub>DS</sub> = 50 V 2N6764			65	
V <sub>GS</sub> = 10 V, I <sub>D</sub> = 30.0 A, V <sub>DS</sub> = 100 V 2N6766			60	
V <sub>GS</sub> = 10 V, I <sub>D</sub> = 14.0 A, V <sub>DS</sub> = 200 V 2N6768			65	
V <sub>GS</sub> = 10 V, I <sub>D</sub> = 12.0 A, V <sub>DS</sub> = 250 V 2N6770			70	

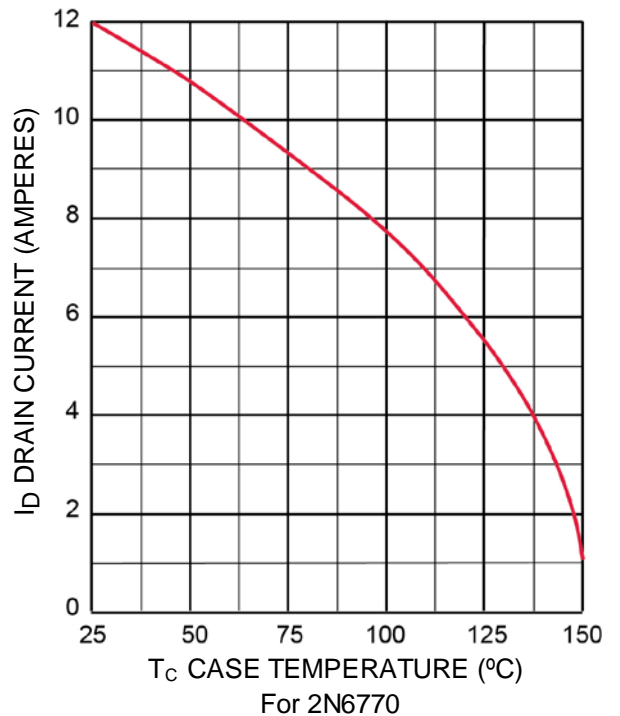
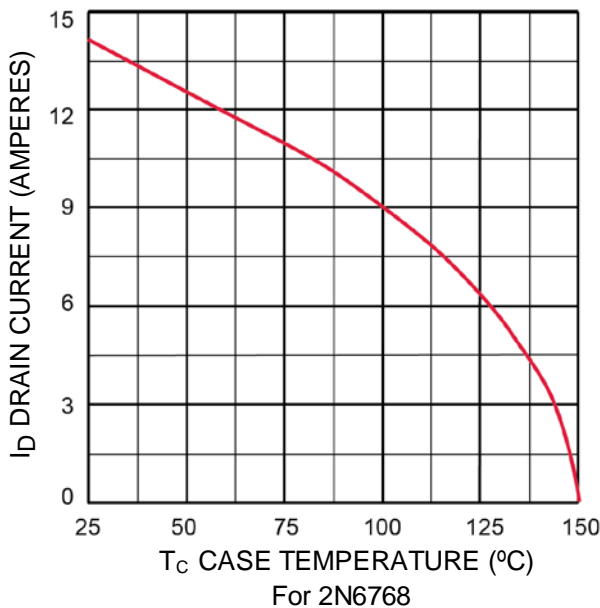
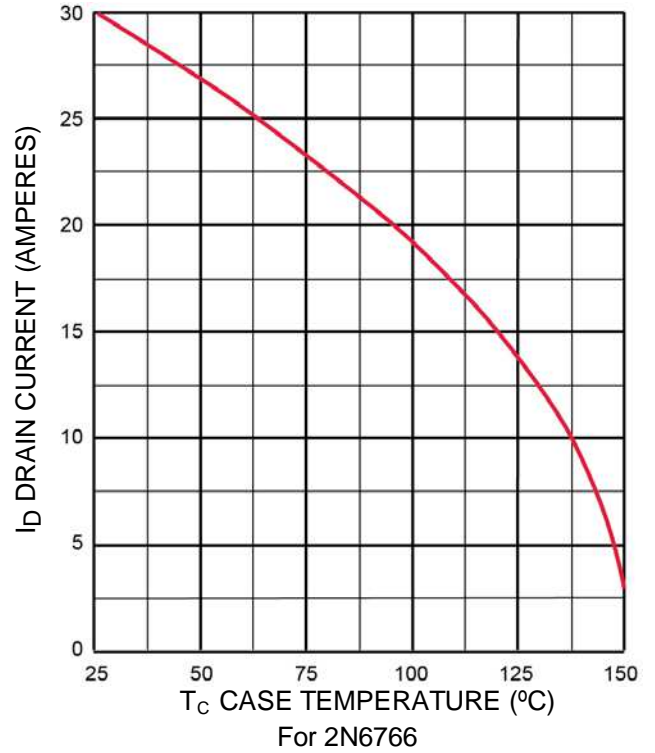
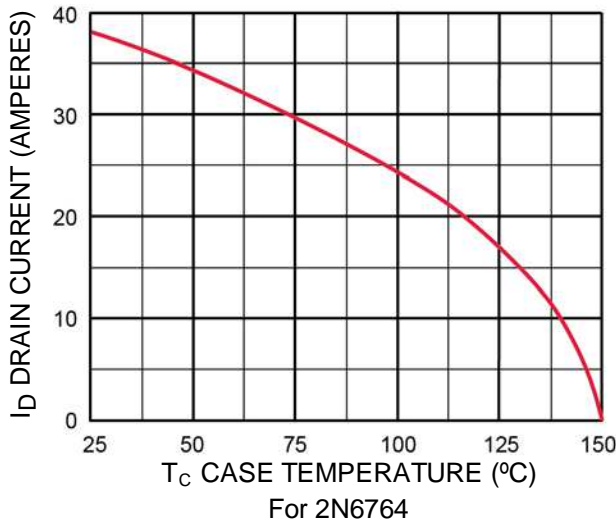
**SWITCHING CHARACTERISTICS**

Parameters / Test Conditions	Symbol	Min.	Max.	Unit
<b>Turn-on delay time</b>				
I <sub>D</sub> = 38.0 A, V <sub>GS</sub> = 10 V, R <sub>G</sub> = 2.35 Ω, V <sub>DD</sub> = 50 V 2N6764	t <sub>d(on)</sub>		35	ns
I <sub>D</sub> = 30.0 A, V <sub>GS</sub> = 10 V, R <sub>G</sub> = 2.35 Ω, V <sub>DD</sub> = 100 V 2N6766				
I <sub>D</sub> = 14.0 A, V <sub>GS</sub> = 10 V, R <sub>G</sub> = 2.35 Ω, V <sub>DD</sub> = 200 V 2N6768				
I <sub>D</sub> = 12.0 A, V <sub>GS</sub> = 10 V, R <sub>G</sub> = 2.35 Ω, V <sub>DD</sub> = 250 V 2N6770				
<b>Rise time</b>				
I <sub>D</sub> = 38.0 A, V <sub>GS</sub> = 10 V, R <sub>G</sub> = 2.35 Ω, V <sub>DD</sub> = 50 V 2N6764	t <sub>r</sub>		190	ns
I <sub>D</sub> = 30.0 A, V <sub>GS</sub> = 10 V, R <sub>G</sub> = 2.35 Ω, V <sub>DD</sub> = 100 V 2N6766				
I <sub>D</sub> = 14.0 A, V <sub>GS</sub> = 10 V, R <sub>G</sub> = 2.35 Ω, V <sub>DD</sub> = 200 V 2N6768				
I <sub>D</sub> = 12.0 A, V <sub>GS</sub> = 10 V, R <sub>G</sub> = 2.35 Ω, V <sub>DD</sub> = 250 V 2N6770				
<b>Turn-off delay time</b>				
I <sub>D</sub> = 38.0 A, V <sub>GS</sub> = 10 V, R <sub>G</sub> = 2.35 Ω, V <sub>DD</sub> = 50 V 2N6764	t <sub>d(off)</sub>		170	ns
I <sub>D</sub> = 30.0 A, V <sub>GS</sub> = 10 V, R <sub>G</sub> = 2.35 Ω, V <sub>DD</sub> = 100 V 2N6766				
I <sub>D</sub> = 14.0 A, V <sub>GS</sub> = 10 V, R <sub>G</sub> = 2.35 Ω, V <sub>DD</sub> = 200 V 2N6768				
I <sub>D</sub> = 12.0 A, V <sub>GS</sub> = 10 V, R <sub>G</sub> = 2.35 Ω, V <sub>DD</sub> = 250 V 2N6770				
<b>Fall time</b>				
I <sub>D</sub> = 38.0 A, V <sub>GS</sub> = 10 V, R <sub>G</sub> = 2.35 Ω, V <sub>DD</sub> = 50 V 2N6764	t <sub>f</sub>		130	ns
I <sub>D</sub> = 30.0 A, V <sub>GS</sub> = 10 V, R <sub>G</sub> = 2.35 Ω, V <sub>DD</sub> = 100 V 2N6766				
I <sub>D</sub> = 14.0 A, V <sub>GS</sub> = 10 V, R <sub>G</sub> = 2.35 Ω, V <sub>DD</sub> = 200 V 2N6768				
I <sub>D</sub> = 12.0 A, V <sub>GS</sub> = 10 V, R <sub>G</sub> = 2.35 Ω, V <sub>DD</sub> = 250 V 2N6770				
<b>Diode Reverse Recovery Time</b>				
di/dt = 100 A/μs, V <sub>DD</sub> ≤ 30 V, I <sub>D</sub> = 38.0 A 2N6764	t <sub>rr</sub>		500	ns
di/dt = 100 A/μs, V <sub>DD</sub> ≤ 30 V, I <sub>D</sub> = 30.0 A 2N6766			950	
di/dt = 100 A/μs, V <sub>DD</sub> ≤ 30 V, I <sub>D</sub> = 14.0 A 2N6768			1200	
di/dt = 100 A/μs, V <sub>DD</sub> ≤ 30 V, I <sub>D</sub> = 12.0 A 2N6770			1600	

GRAPHS



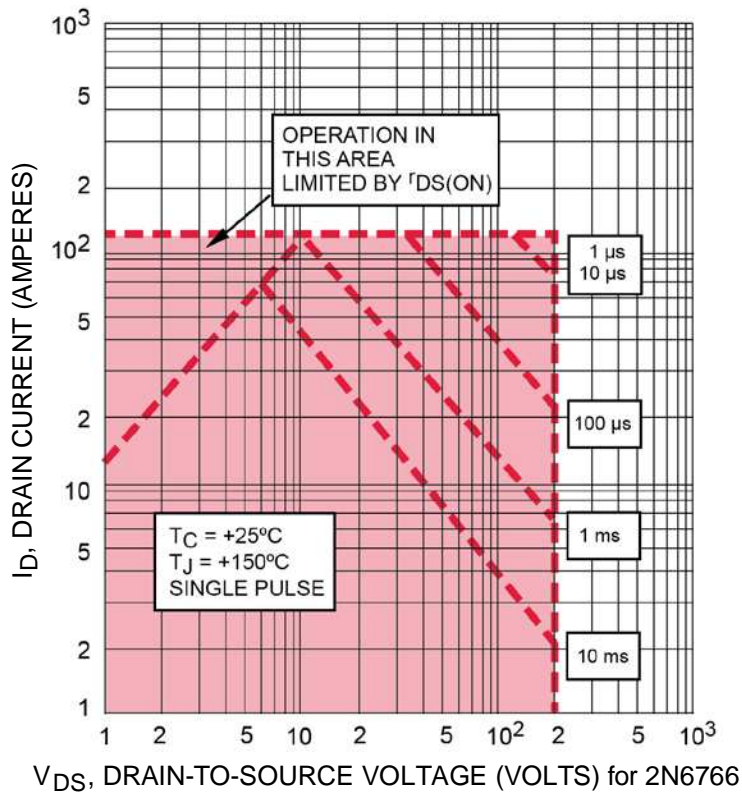
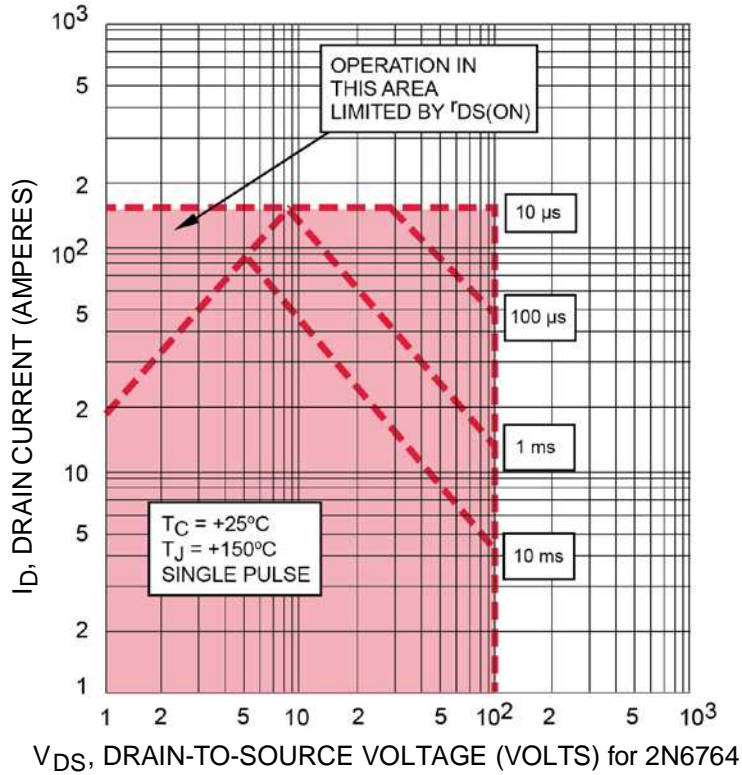
**FIGURE 1**  
Thermal Response Curves

**GRAPHS (continued)**
**FIGURE 2 – Maximum Drain Current vs Case Temperature Graphs**


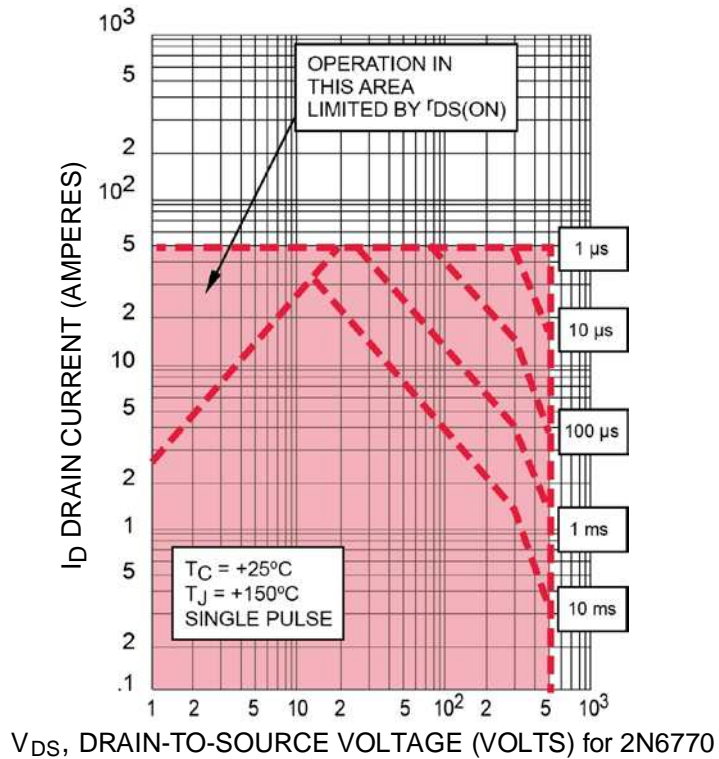
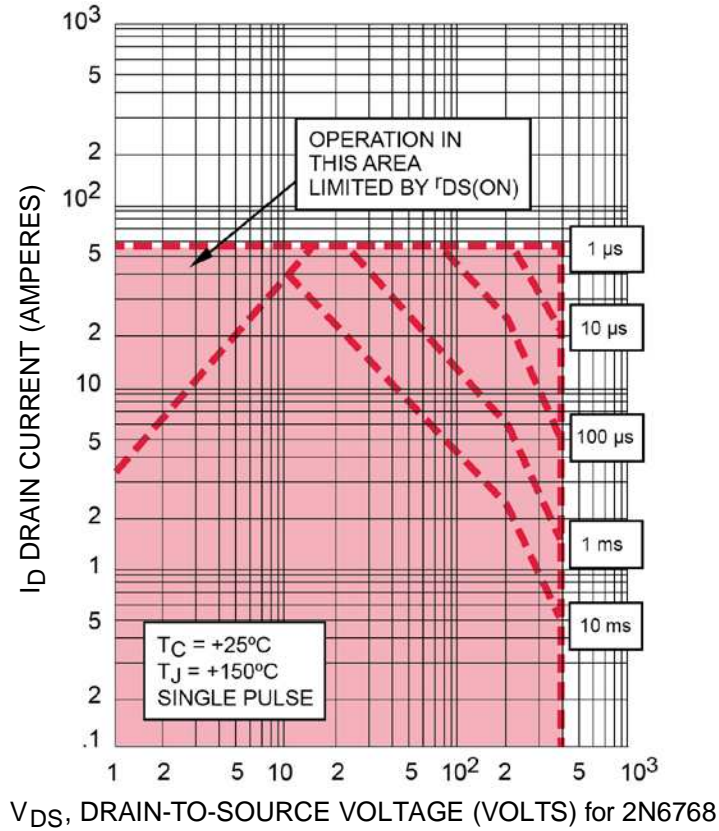


GRAPHS (continued)

FIGURE 3 – Maximum Safe Operating Area

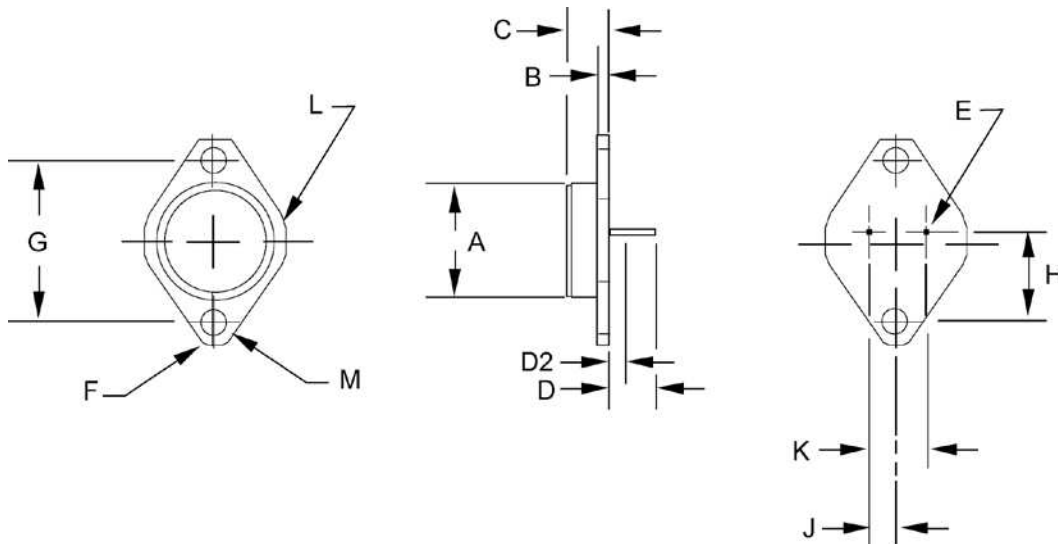


GRAPHS (continued)





PACKAGE DIMENSIONS



**NOTE:**

1. Dimensions are in inches.
2. Millimeters are given for general information only.
3. These dimensions should be measured at points .050 inch (1.27 mm) and .055 inch (1.40 mm) below the seating plane. When gauge is not used measurement will be made at the seating plane.
4. The seating plane of the header shall be flat within .001 inch (0.03 mm) concave to .004 inch (0.10 mm) convex inside a .930 inch (23.62 mm) diameter circle on the center of the header and flat within .001 inch (0.03 mm) concave to .006 inch (0.15 mm) convex overall.
5. These dimensions pertain to the 2N6764 and 2N6766 types.
6. These dimensions pertain to the 2N6768 and 2N6770 types.
7. Mounting holes shall be deburred on the seating plane side.
8. Drain is electrically connected to the case.
9. In accordance with ASME Y14.5M, diameters are equivalent to  $\Phi$ x symbology.

DIM	INCHES		MILLIMETERS		NOTES
	MIN	MAX	MIN	MAX	
A	-	0.875	-	22.23	
B	0.060	0.135	1.52	3.43	
C	0.250	0.360	6.35	9.15	
D	0.312	0.500	7.92	12.70	
D2	-	0.050	-	1.27	(3)
E	0.057	0.063	1.45	1.60	DIA. (5)
	0.038	0.043	0.97	1.10	DIA. (6)
F	0.131	0.188	3.33	4.78	Radius
G	1.177	1.197	29.90	30.40	
H	0.655	0.675	16.64	17.15	
J	0.205	0.225	5.21	5.72	
K	0.420	0.440	10.67	11.18	
L	0.495	0.525	12.57	13.3	Radius
M	0.151	0.161	3.84	4.09	DIA. (7)

SCHMATIC

